

L Number	Hits	Search Text	DB	Time stamp
1	2	("6512246").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:25
3	3	("6093586"   "6232142"   "6358766"   "2002/0048869").PN.	USPAT;	2004/05/26 11:59
4	4144	438/48,128,149,151,157,283.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:26
5	3890	257/59,72,82,382,383.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:26
6	7853	438/48,128,149,151,157,283.ccls. or 257/59,72,82,382,383.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:26
7	2841	(438/48,128,149,151,157,283.ccls. or 257/59,72,82,382,383.ccls.) and ((thin near film near transistor\$1) TFT\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:50
8	0	((438/48,128,149,151,157,283.ccls. or 257/59,72,82,382,383.ccls.) and ((thin near film near transistor\$1) TFT\$1)) and ((semiconductor near (layer film)) near on near substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:28
9	732	((438/48,128,149,151,157,283.ccls. or 257/59,72,82,382,383.ccls.) and ((thin near film near transistor\$1) TFT\$1)) and ((semiconductor near (layer film)) near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:41
10	10	((438/48,128,149,151,157,283.ccls. or 257/59,72,82,382,383.ccls.) and ((thin near film near transistor\$1) TFT\$1)) and ((semiconductor near (layer film)) near2 substrate)) and (((thermal\$2 near conduct\$5) cool\$3) near (layer film)) with (semiconductor near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:42
11	344387	257/\$.ccls. 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:41
12	12266	(257/\$.ccls. 438/\$.ccls.) and ((thin near film near transistor\$1) TFT\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:41
13	2212	((257/\$.ccls. 438/\$.ccls.) and ((thin near film near transistor\$1) TFT\$1)) and ((semiconductor near (layer film)) near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:50
14	0	((257/\$.ccls. 438/\$.ccls.) and ((thin near film near transistor\$1) TFT\$1)) and ((semiconductor near (layer film)) near2 substrate)) and (((thermal\$2 near conduct\$5) cool\$3) near (layer film)) near5 on near2 (semiconductor near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:43

15	18	(((257/\$.ccls. 438/\$.ccls.) and ((thin near film near transistor\$1) TFT\$1)) and ((semiconductor near (layer film)) near2 substrate)) and (((thermal\$2 near conduct\$5) cool\$3) near (layer film)) near2 (semiconductor near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:49
16	19	(((257/\$.ccls. 438/\$.ccls.) and ((thin near film near transistor\$1) TFT\$1)) and ((semiconductor near (layer film)) near2 substrate)) and (((thermal\$2 near conduct\$5) cool\$3 tungsten) near (layer film)) near2 (semiconductor near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:51
17	62243	(thin near film near transistor\$1) TFT\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:50
18	3268	((thin near film near transistor\$1) TFT\$1) and ((semiconductor near (layer film)) near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:51
19	19	(((thin near film near transistor\$1) TFT\$1) and ((semiconductor near (layer film)) near2 substrate)) and (((thermal\$2 near conduct\$5) cool\$3 tungsten) near (layer film)) near2 (semiconductor near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:51
20	30	((thin near film near transistor\$1) TFT\$1) and (((thermal\$2 near conduct\$5) cool\$3 tungsten) near (layer film)) near2 (semiconductor near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 12:59
21	46	((thin near film near transistor\$1) TFT\$1) and (((thermal\$2 near conduct\$5) cool\$3 tungsten) near (layer film)) near5 (semiconductor near (layer film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/26 13:00